

ATTY. DOCKET NO.
006301 USA/
Consilium/Consilium

SERIAL NO.
09/928,474

APPLICANT
Badri N. KRISHNAMURTHY et al.

FILING DATE
August 14, 2001

GROUP
2812

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September 16, 2004. International Preliminary Examination Report for PCT Serial No. PCT/US02/24859.

EXAMINER

DATE CONSIDERED

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SHEET 2 OF 2

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 006301 USA/ Consilium/Consilium		SERIAL NO. 09/928,474	
				APPLICANT Badri N. KRISHNAMURTHY et al.			
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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
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<i>JS</i>	5,369,544	11/29/94	Mastrangelo			04/05/93	
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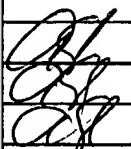








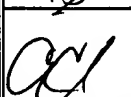


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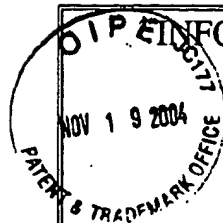
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